

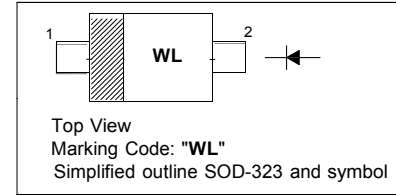
BAND SWITCHING DIODE

Features

- Very small plastic SMD package
- Low diode capacitance
- Low diode forward resistance
- Small inductance

PINNING

| PIN | DESCRIPTION |
|-----|-------------|
| 1 | Cathode |
| 2 | Anode |

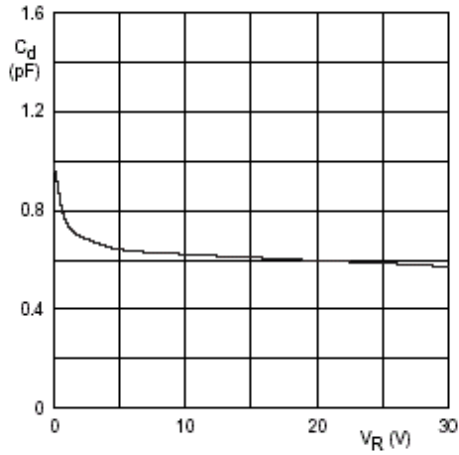


Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

| Parameter | Symbol | Value | Unit |
|--------------------------------------|-----------|---------------|------------------|
| Continuous Reverse Voltage | V_R | 35 | V |
| Continuous Forward Current | I_F | 100 | mA |
| Power Dissipation | P_{tot} | 500 | mW |
| Operating Junction Temperature Range | T_J | - 65 to + 150 | $^\circ\text{C}$ |
| Storage Temperature Range | T_{stg} | - 65 to + 150 | $^\circ\text{C}$ |

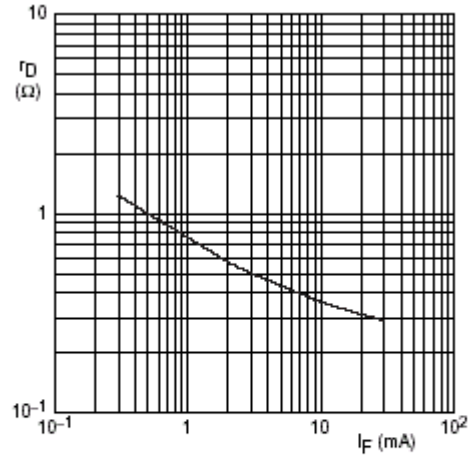
Electrical Characteristics at $T_a = 25\text{ }^\circ\text{C}$

| Parameter | Symbol | Typ. | Max. | Unit |
|---|---------|--------|-------------|------------|
| Forward Voltage at $I_F = 10\text{ mA}$ | V_F | - | 1 | V |
| Reverse Current at $V_R = 20\text{ V}$ | I_R | - | 20 | nA |
| Diode Capacitance at $V_R = 1\text{ V}$, $f = 1\text{ MHz}$ at $V_R = 3\text{ V}$, $f = 1\text{ MHz}$ | C_D | - - | 1.05 0.9 | pF |
| Diode Forward Resistance at $I_F = 3\text{ mA}$, $f = 100\text{ MHz}$ at $I_F = 10\text{ mA}$, $f = 100\text{ MHz}$ | r_D | - - | 0.7 0.5 | Ω |
| Reverse Resistance at $V_R = 1\text{ V}$, $f = 100\text{ MHz}$ | $1/g_p$ | 100 | - | K Ω |
| Series Inductance | L_s | 2 | - | nH |



$f = 1 \text{ MHz}; T_j = 25 \text{ }^\circ\text{C}.$

Fig.2 Diode capacitance as a function of reverse voltage; typical values.



$f = 100 \text{ MHz}; T_j = 25 \text{ }^\circ\text{C}.$

Diode forward resistance as a function of forward current; typical values.